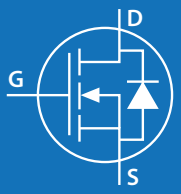
EPC2012C – Enhancement Mode Power Transistor

V_{DS} , 200 V
$R_{DS\ (on)}$, 100 mΩ
I_D , 5 A



EFFICIENT POWER CONVERSION

RoHS Halogen-Free

Revised April 22, 2021

Gallium Nitride's exceptionally high electron mobility and low temperature coefficient allows very low $R_{DS(on)}$, while its lateral device structure and majority carrier diode provide exceptionally low Q_G and zero Q_{RR}. The end result is a device that can handle tasks where very high switching frequency, and low on-time are beneficial as well as those where on-state losses dominate.

Questions: Ask a GaN Expert

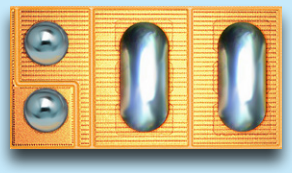
Maximum Ratings			
PARAMETER		**VALUE**	**UNIT**
V_{DS}	Drain-to-Source Voltage (Continuous)	200	V
I_D	Continuous (T_A = 25°C, $R_{\theta JA}$ = 26°C/W)	5	A
	Pulsed (25°C, T_{PULSE} = 300 µs)	22	
V_{GS}	Gate-to-Source Voltage	6	V
	Gate-to-Source Voltage	-4	
T_J	Operating Temperature	-40 to 150	°C
T_{STG}	Storage Temperature	-40 to 150	

Thermal Characteristics			
PARAMETER		**TYP**	**UNIT**
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	4.2	°C/W
$R_{\theta JB}$	Thermal Resistance, Junction-to-Board	12.5	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	85	

Note 1: $R_{\theta JA}$ is determined with the device mounted on one square inch of copper pad, single layer 2 oz copper on FR4 board.
See https://epc-co.com/epc/documents/product-training/Appnote_Thermal_Performance_of_eGaN_FETs.pdf for details.

Static Characteristics (T_J = 25°C unless otherwise stated)						
PARAMETER		**TEST CONDITIONS**	**MIN**	**TYP**	**MAX**	**UNIT**
BV_{DSS}	Drain-to-Source Voltage	V_{GS} = 0 V, I_D = 60 µA	200			V
I_{DSS}	Drain-Source Leakage	V_{GS} = 0 V, V_{DS} = 160 V		10	50	µA
I_{GSS}	Gate-to-Source Forward Leakage	V_{GS} = 5 V		0.2	1	mA
	Gate-to-Source Reverse Leakage	V_{GS} = -4 V		10	50	µA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 1 mA	0.8	1.4	2.5	V
$R_{DS(on)}$	Drain-Source On Resistance	V_{GS} = 5 V, I_D = 3 A		70	100	mΩ
V_{SD}	Source-Drain Forward Voltage#	V_{GS} = 0 V, I_S = 0.5 A		1.9		V

Defined by design. Not subject to production test.
All measurements were done with substrate connected to source.



Die size: 1.7 x 0.9 mm

EPC2012C eGaN® FETs are supplied only in passivated die form with solder bars.

Applications

- High frequency DC-DC conversion
- Class D audio
- Wireless power transfer

Benefits

- Ultra high efficiency
- Ultra low $R_{DS(on)}$
- Ultra low Q_G
- Ultra small footprint

Scan QR code or click link below for more information including reliability reports, device models, demo boards!

https://l.ead.me/EPC2012C

Dynamic Characteristics# (T_J = 25°C unless otherwise stated)						
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
C_{ISS}	Input Capacitance	V_{GS} = 0 V, V_{DS} = 100 V		100	140	pF
C_{RSS}	Reverse Transfer Capacitance			0.4	0.6	
C_{OSS}	Output Capacitance			64	85	
R_G	Gate Resistance			0.6		Ω
Q_G	Total Gate Charge	V_{GS} = 5 V, V_{DS} = 100 V, I_D = 3 A		1	1.3	nC
Q_{GS}	Gate-to-Source Charge	V_{DS} = 100 V, I_D = 3 A		0.3		
Q_{GD}	Gate-to-Drain Charge			0.2	0.35	
$Q_{G(TH)}$	Gate Charge at Threshold			0.2		
Q_{OSS}	Output Charge	V_{GS} = 0 V, V_{DS} = 100 V		10	13	
Q_{RR}	Source-Drain Recovery Charge			0		

Defined by design. Not subject to production test.
All measurements were done with substrate connected to source.
Note 2: $C_{OSS(ER)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 50% BV_{DSS}.
Note 3: $C_{OSS(TR)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 50% BV_{DSS}.

Figure 1: Typical Output Characteristics at 25°C

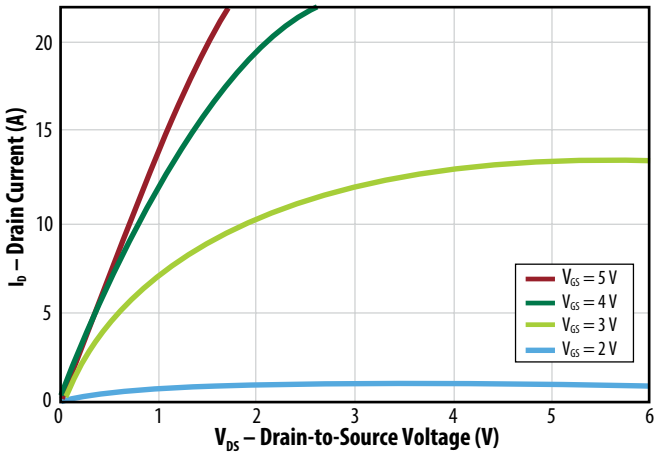


Figure 2: Typical Transfer Characteristics

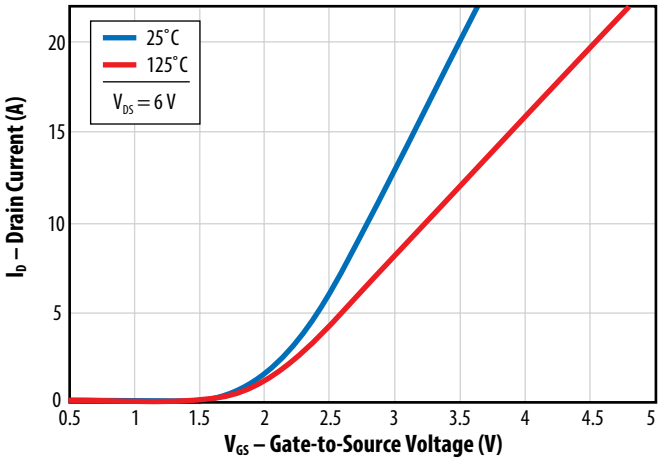


Figure 3: Typical $R_{DS(on)}$ vs. V_{GS} for Various Drain Currents

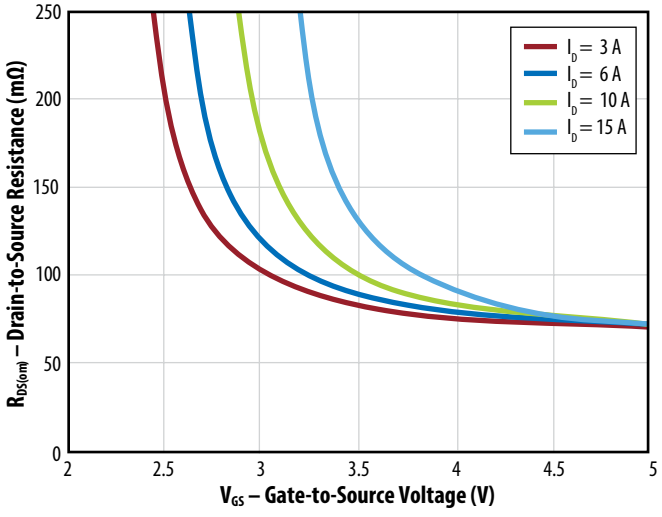


Figure 4: Typical $R_{DS(on)}$ vs. V_{GS} for Various Temperatures

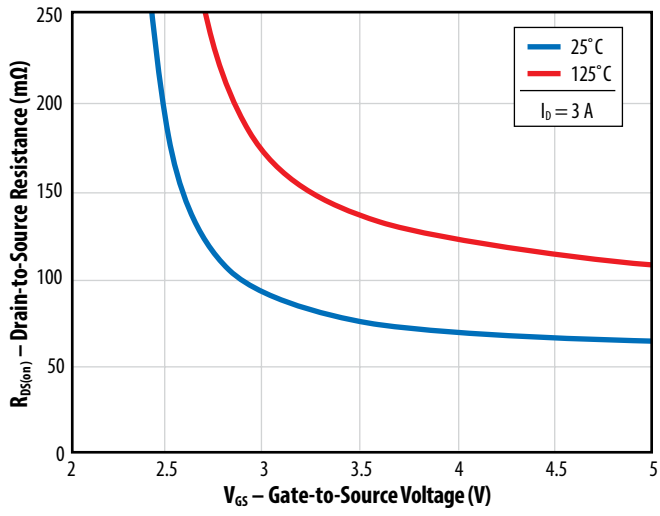


Figure 5a: Typical Capacitance (Linear Scale)

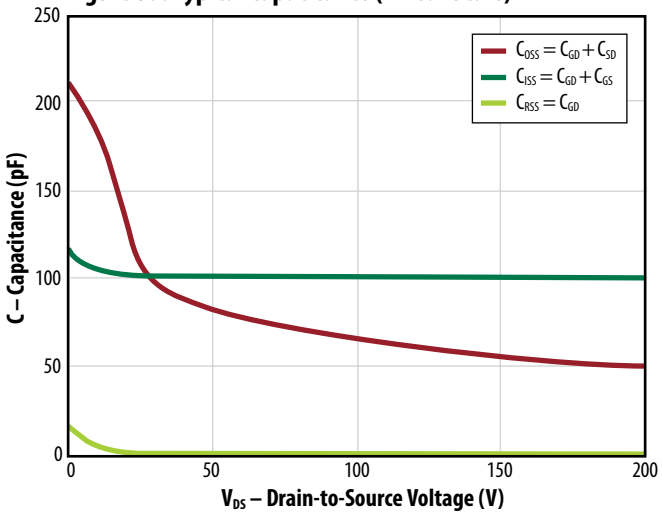


Figure 5b: Typical Capacitance (Log Scale)

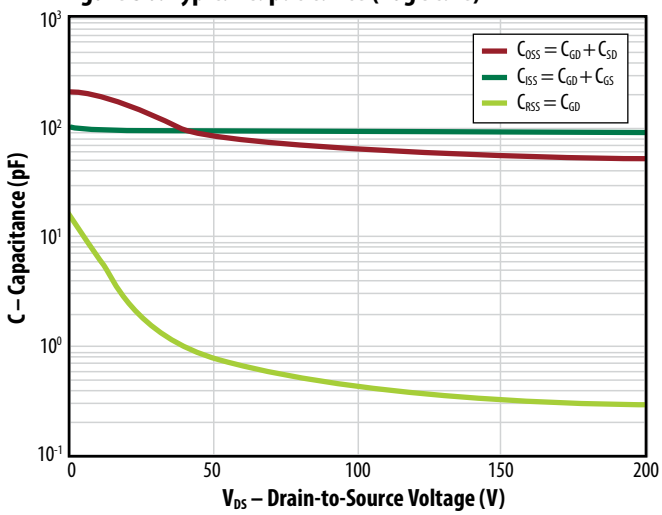


Figure 6: Typical Gate Charge

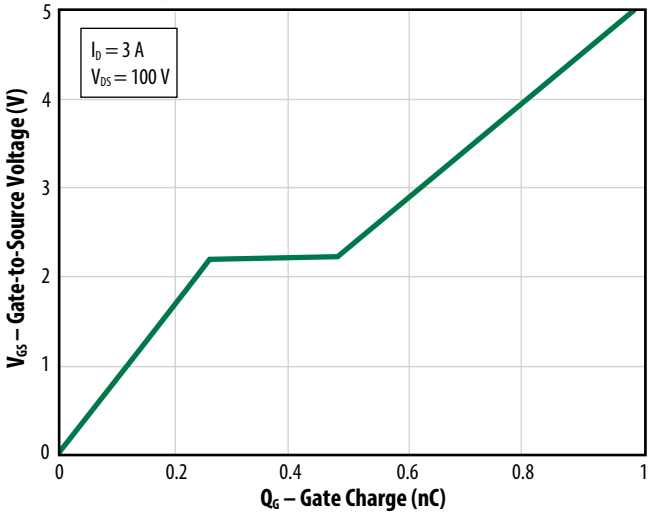
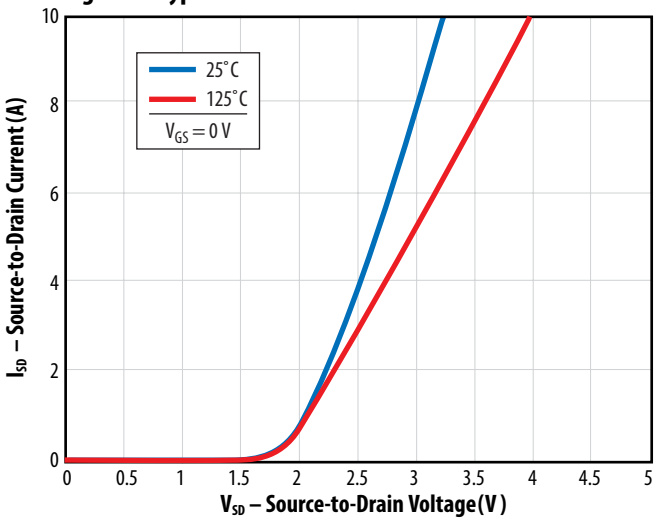


Figure 7: Typical Reverse Drain-Source Characteristics



Note: Negative gate drive voltage increases the reverse drain-source voltage. EPC recommends 0 V for OFF.

Figure 8: Typical Normalized On Resistance vs. Temperature

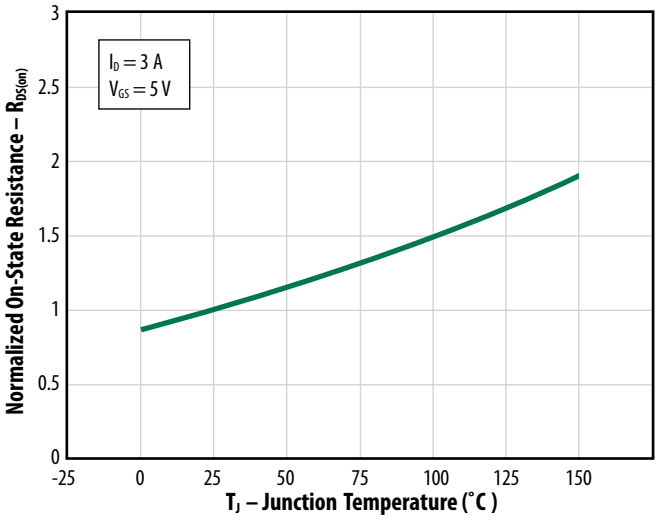


Figure 9: Typical Normalized Threshold Voltage vs. Temp.

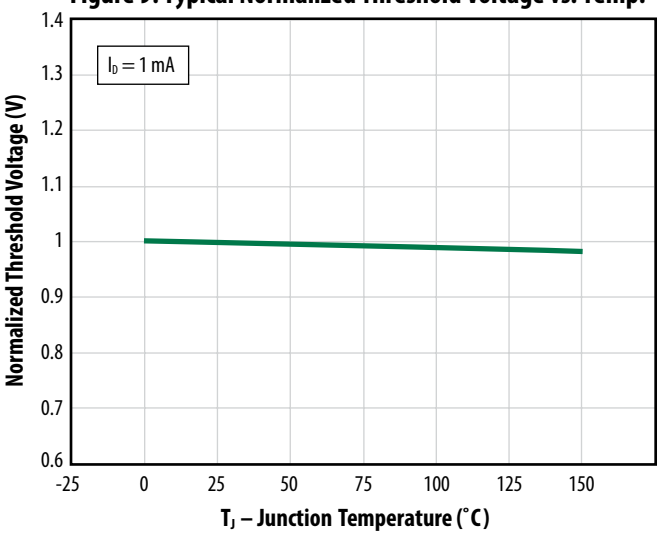


Figure 10: Typical Gate Current

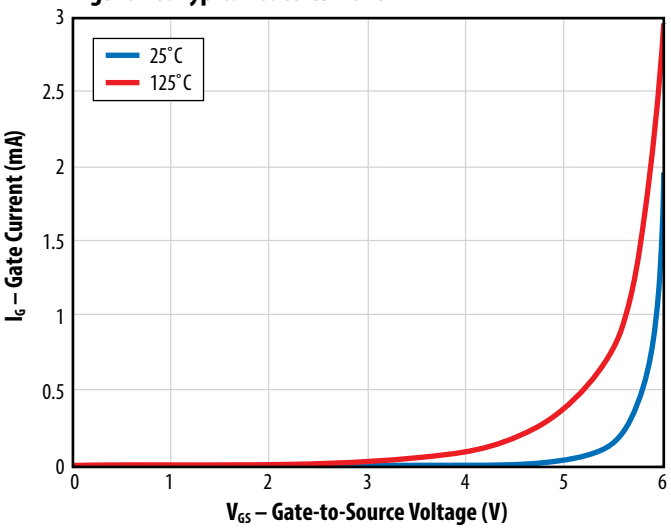
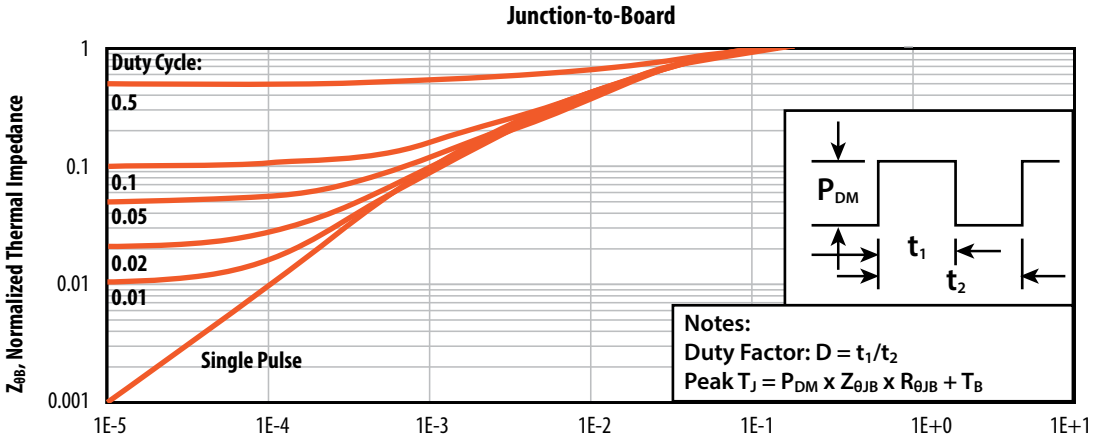


Figure 11: Typical Transient Thermal Response Curves



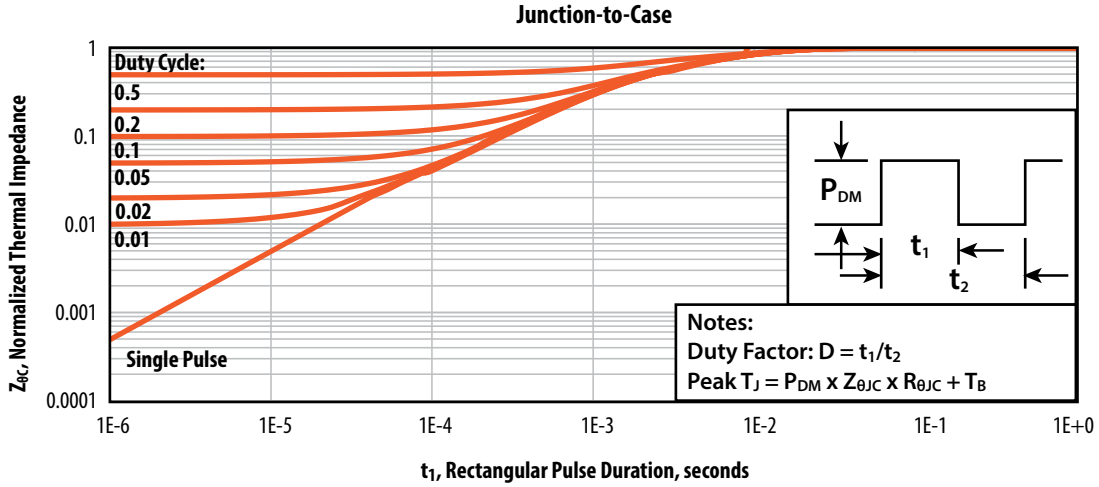
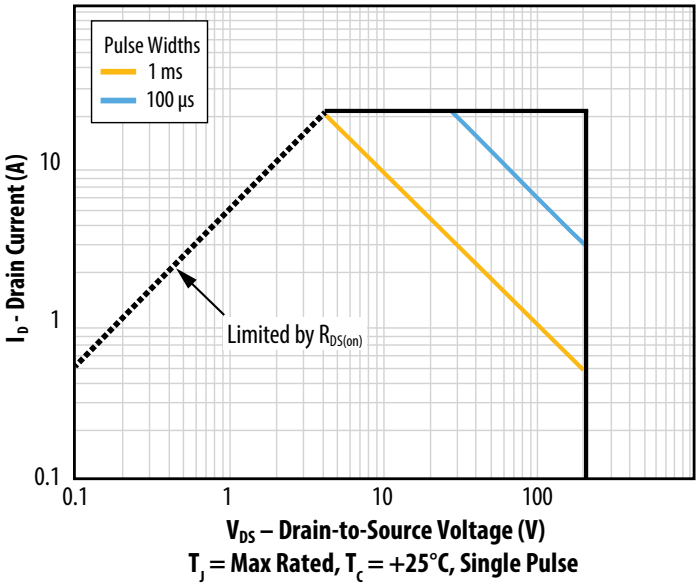
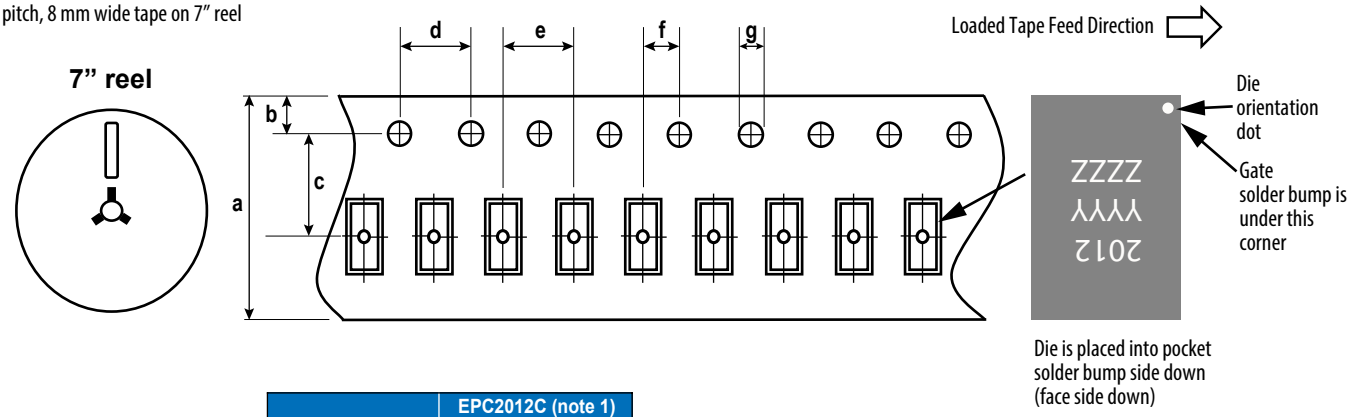


Figure 12: Safe Operating Area



TAPE AND REEL CONFIGURATION

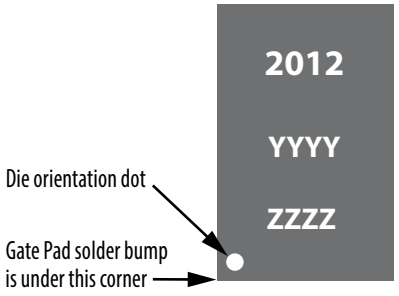
4 mm pitch, 8 mm wide tape on 7" reel



	EPC2012C (note 1)		
Dimension (mm)	target	min	max
a	8.00	7.90	8.30
b	1.75	1.65	1.85
c (note 2)	3.50	3.45	3.55
d	4.00	3.90	4.10
e	4.00	3.90	4.10
f (note 2)	2.00	1.95	2.05
g	1.5	1.5	1.6

Note 1: MSL 1 (moisture sensitivity level 1) classified according to IPC/JEDEC industry standard.
Note 2: Pocket position is relative to the sprocket hole measured as true position of the pocket, not the pocket hole.

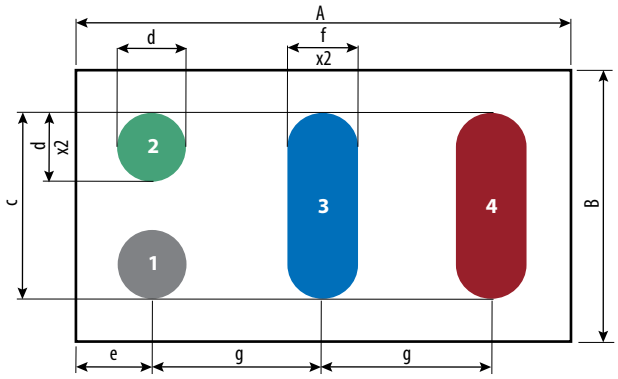
DIE MARKINGS



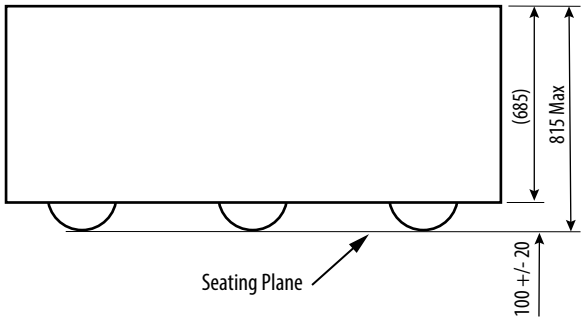
Part Number	Laser Markings		
	Part # Marking Line 1	Lot_Date Code Marking line 2	Lot_Date Code Marking Line 3
EPC2012C	2012	YYYY	ZZZZ

DIE OUTLINE

Solder Bar View



Side View



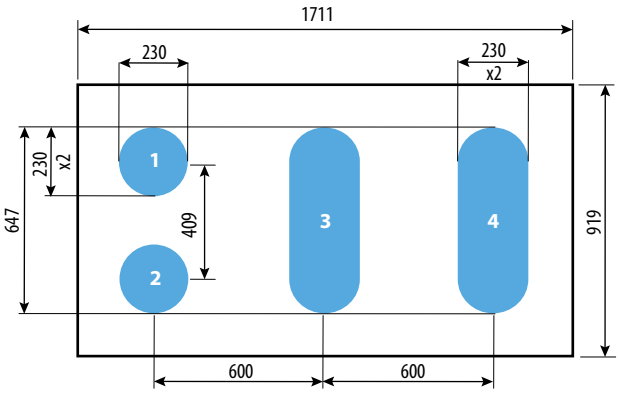
DIM	MICROMETERS		
	MIN	Nominal	MAX
A	1681	1711	1741
B	889	919	949
c	662	667	672
d	245	250	255
e	230	245	260
f	245	250	255
g	600	600	600

Pad no. 1 is Gate;
Pad no. 2 is Substrate;*
Pad no. 3 is Drain;
Pad no. 4 is Source

*Substrate pin should be connected to Source

RECOMMENDED LAND PATTERN

(units in µm)



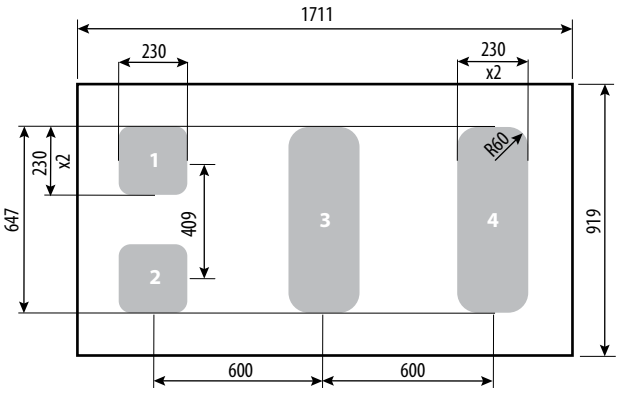
The land pattern is solder mask defined.

Pad no. 1 is Gate;
Pad no. 2 is Substrate;*
Pad no. 3 is Drain;
Pad no. 4 is Source

*Substrate pin should be connected to Source

RECOMMENDED STENCIL DRAWING

(units in µm)



Recommended stencil should be 4 mil (100 µm) thick, must be laser cut , opening per drawing. The corner has a radius of R60.

Intended for use with SAC305 Type 4 solder, reference 88.5% metals content.

Additional assembly resources available at https://epc-co.com/epc/design-support

Efficient Power Conversion Corporation (EPC) reserves the right to make changes without further notice to any products herein to improve reliability, function or design. EPC does not assume any liability arising out of the application or use of any product or circuit described herein; neither does it convey any license under its patent rights, nor the rights of others.
eGaN® is a registered trademark of Efficient Power Conversion Corporation.
EPC Patent Listing: https://epc-co.com/epc/about-epc/patents
Information subject to change without notice.

ENTEGRECİ

Bu belge www.entegreci.com üzerinden sunulmaktadır.

Elektronik komponent tedarikinde Entegreci

Entegreci, Eskişehir merkezli, Türkiye geneline satış yapan bir elektronik komponent mağazasıdır. Entegreler (IC), mikrodenetleyiciler, transistörler, diyotlar, pasif elemanlar, konnektörler, modüller ve geliştirme kartları tek adetten seri üretim adetlerine kadar satılır. Ürün sayfalarında güncel stok durumunu, fiyatı ve datasheet bağlantısını bulabilirsiniz.

Parça koduyla arama

Üretici parça numarasını yazın; stok ve fiyatı hemen görün.

www.entegreci.com

Ürün kategorileri

Entegreden kapasitöre tüm elektronik komponent kategorileri.

Kategorilere göz atın

Üreticiler

Aradığınız üreticinin ürünlerini tek sayfada inceleyin.

Üreticileri görün

Toplu alım ve teklif

Listede olmayan ya da yüksek adetli parçalar için teklif isteyin.

Teklif isteyin

www.entegreci.com | **destek@entegreci.com** | **0850 305 90 34**

Entegreci is an online electronic components store based in Türkiye. Search by manufacturer part number to see stock, prices and datasheets for integrated circuits, microcontrollers, transistors, passive components and connectors, or request a quote for parts that are not listed.

Bu sayfa Entegreci tarafından eklenmiştir. Belgenin önceki sayfaları asıl yayıncısına aittir ve içeriği değiştirilmemiştir; en güncel sürüm için belgenin yayıncısına başvurun.